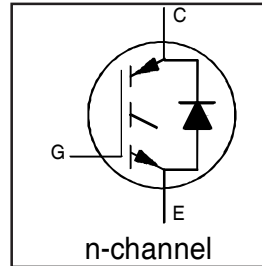


# IRG4PH40UD

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE UltraFast CoPack IGBT

## Features

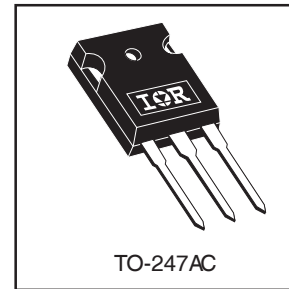
- UltraFast: Optimized for high operating frequencies up to 40 kHz in hard switching, >200 kHz in resonant mode
- New IGBT design provides tighter parameter distribution and higher efficiency than previous generations
- IGBT co-packaged with HEXFRED™ ultrafast, ultra-soft-recovery anti-parallel diodes for use in bridge configurations
- Industry standard TO-247AC package



$V_{CES} = 1200V$
$V_{CE(on) typ.} = 2.43V$
@ $V_{GE} = 15V, I_C = 21A$

## Benefits

- Higher switching frequency capability than competitive IGBTs
- Highest efficiency available
- HEXFRED diodes optimized for performance with IGBT's. Minimized recovery characteristics require less/no snubbing



## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Breakdown Voltage	1200	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	41	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	21	
$I_{CM}$	Pulsed Collector Current ①	82	
$I_{LM}$	Clamped Inductive Load Current ②	82	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	8.0	
$I_{FM}$	Diode Maximum Forward Current	130	
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	160	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	65	
$T_J$	Operating Junction and Storage Temperature Range	-55 to + 150	°C
$T_{STG}$			
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

## Thermal Resistance

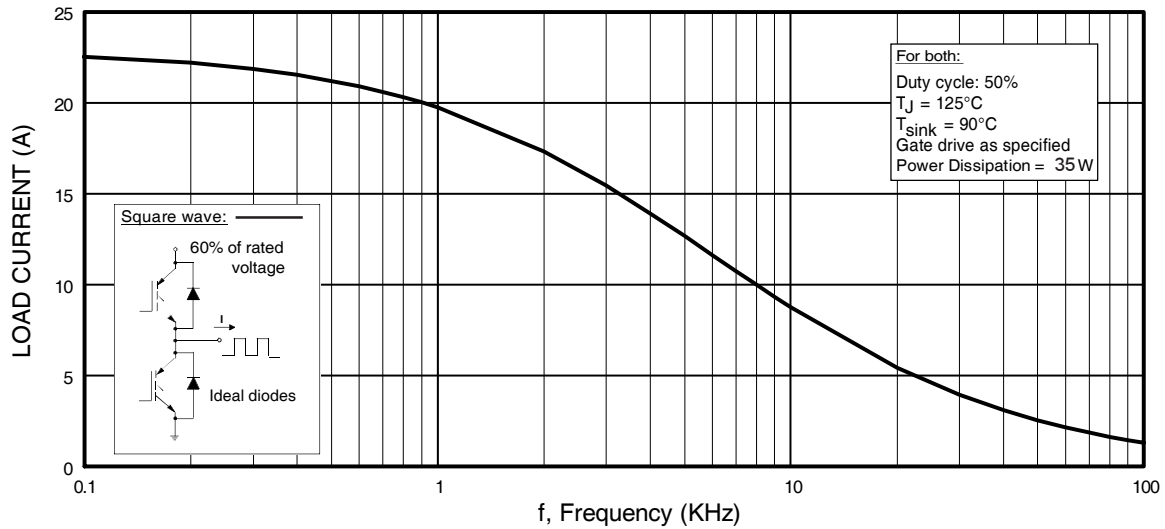
	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	---	---	0.77	°C/W
$R_{\theta JC}$	Junction-to-Case - Diode	---	---	1.7	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	---	0.24	---	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	---	---	40	
Wt	Weight	---	6 (0.21)	---	g (oz)

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

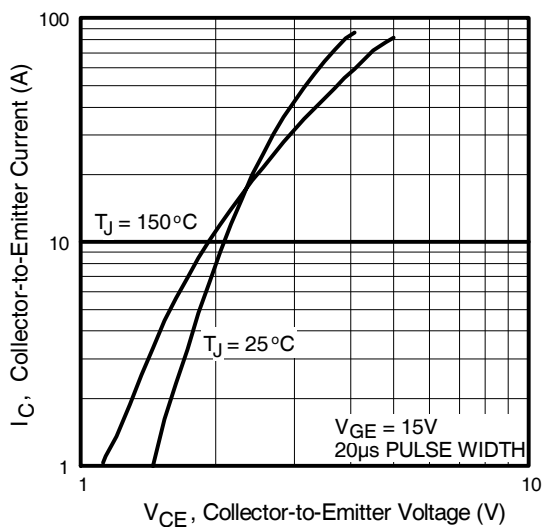
	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)CES</sub>	Collector-to-Emitter Breakdown Voltage <sup>③</sup>	1200	—	—	V	V <sub>GE</sub> = 0V, I <sub>C</sub> = 250μA
ΔV <sub>(BR)CES</sub> /ΔT <sub>J</sub>	Temperature Coeff. of Breakdown Voltage	—	0.43	—	V/°C	V <sub>GE</sub> = 0V, I <sub>C</sub> = 1.0mA
V <sub>CE(on)</sub>	Collector-to-Emitter Saturation Voltage	—	2.43	3.1	V	I <sub>C</sub> = 21A V <sub>GE</sub> = 15V
		—	2.97	—		I <sub>C</sub> = 41A See Fig. 2, 5
		—	2.47	—		I <sub>C</sub> = 21A, T <sub>J</sub> = 150°C
V <sub>GE(th)</sub>	Gate Threshold Voltage	3.0	—	6.0		V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 250μA
ΔV <sub>GE(th)</sub> /ΔT <sub>J</sub>	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 250μA
g <sub>fe</sub>	Forward Transconductance <sup>④</sup>	16	24	—	S	V <sub>CE</sub> = 100V, I <sub>C</sub> = 21A
I <sub>CES</sub>	Zero Gate Voltage Collector Current	—	—	250	μA	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 1200V
		—	—	5000		V <sub>GE</sub> = 0V, V <sub>CE</sub> = 1200V, T <sub>J</sub> = 150°C
V <sub>FM</sub>	Diode Forward Voltage Drop	—	2.6	3.3	V	I <sub>C</sub> = 8.0A See Fig. 13
		—	2.4	3.1		I <sub>C</sub> = 8.0A, T <sub>J</sub> = 125°C
I <sub>GES</sub>	Gate-to-Emitter Leakage Current	—	—	±100	nA	V <sub>GE</sub> = ±20V

## Switching Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

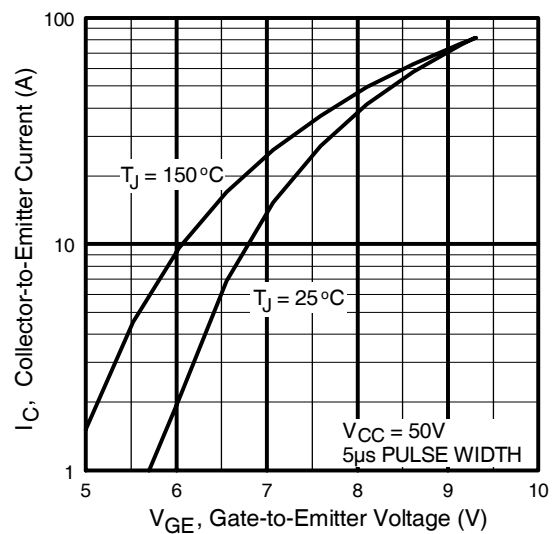
	Parameter	Min.	Typ.	Max.	Units	Conditions
Q <sub>g</sub>	Total Gate Charge (turn-on)	—	86	130	nC	I <sub>C</sub> = 21A V <sub>CC</sub> = 400V See Fig. 8 V <sub>GE</sub> = 15V
Q <sub>ge</sub>	Gate - Emitter Charge (turn-on)	—	13	20		
Q <sub>gc</sub>	Gate - Collector Charge (turn-on)	—	29	44		
t <sub>d(on)</sub>	Turn-On Delay Time	—	46	—	ns	T <sub>J</sub> = 25°C I <sub>C</sub> = 21A, V <sub>CC</sub> = 800V V <sub>GE</sub> = 15V, R <sub>G</sub> = 10Ω Energy losses include "tail" and diode reverse recovery. See Fig. 9, 10, 18
t <sub>r</sub>	Rise Time	—	35	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	97	150		
t <sub>f</sub>	Fall Time	—	240	360		
E <sub>on</sub>	Turn-On Switching Loss	—	1.80	—	mJ	See Fig. 11, 18
E <sub>off</sub>	Turn-Off Switching Loss	—	1.93	—		
E <sub>ts</sub>	Total Switching Loss	—	3.73	4.6		
t <sub>d(on)</sub>	Turn-On Delay Time	—	42	—	ns	T <sub>J</sub> = 150°C, See Fig. 11, 18 I <sub>C</sub> = 21A, V <sub>CC</sub> = 800V V <sub>GE</sub> = 15V, R <sub>G</sub> = 10Ω Energy losses include "tail" and diode reverse recovery.
t <sub>r</sub>	Rise Time	—	32	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	240	—		
t <sub>f</sub>	Fall Time	—	510	—		
E <sub>ts</sub>	Total Switching Loss	—	7.04	—	mJ	Measured 5mm from package
L <sub>E</sub>	Internal Emitter Inductance	—	13	—	nH	
C <sub>ies</sub>	Input Capacitance	—	1800	—	pF	V <sub>GE</sub> = 0V V <sub>CC</sub> = 30V See Fig. 7 f = 1.0MHz
C <sub>oes</sub>	Output Capacitance	—	120	—		
C <sub>res</sub>	Reverse Transfer Capacitance	—	18	—		
t <sub>rr</sub>	Diode Reverse Recovery Time	—	63	95	ns	T <sub>J</sub> = 25°C See Fig. 14
		—	106	160		T <sub>J</sub> = 125°C
I <sub>rr</sub>	Diode Peak Reverse Recovery Current	—	4.5	8.0	A	T <sub>J</sub> = 25°C See Fig. 15
		—	6.2	11		T <sub>J</sub> = 125°C
Q <sub>rr</sub>	Diode Reverse Recovery Charge	—	140	380	nC	T <sub>J</sub> = 25°C See Fig. 16
		—	335	880		T <sub>J</sub> = 125°C
di <sub>(rec)M</sub> /dt	Diode Peak Rate of Fall of Recovery During t <sub>b</sub>	—	133	—	A/μs	T <sub>J</sub> = 25°C See Fig. 17
		—	85	—		T <sub>J</sub> = 125°C



**Fig. 1 - Typical Load Current vs. Frequency**  
 (Load Current =  $I_{\text{RMS}}$  of fundamental)

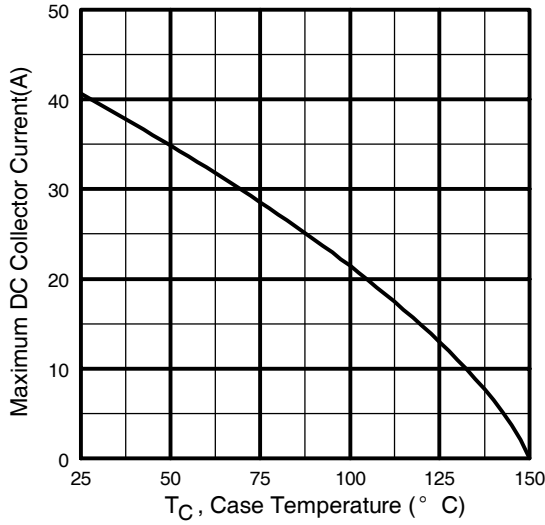


**Fig. 2 - Typical Output Characteristics**  
[www.irf.com](http://www.irf.com)

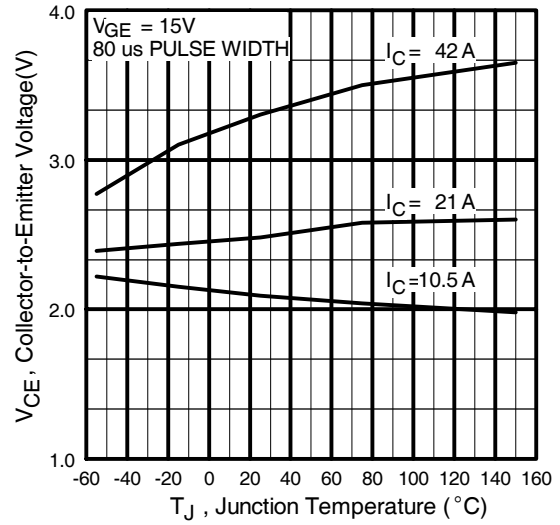


**Fig. 3 - Typical Transfer Characteristics**

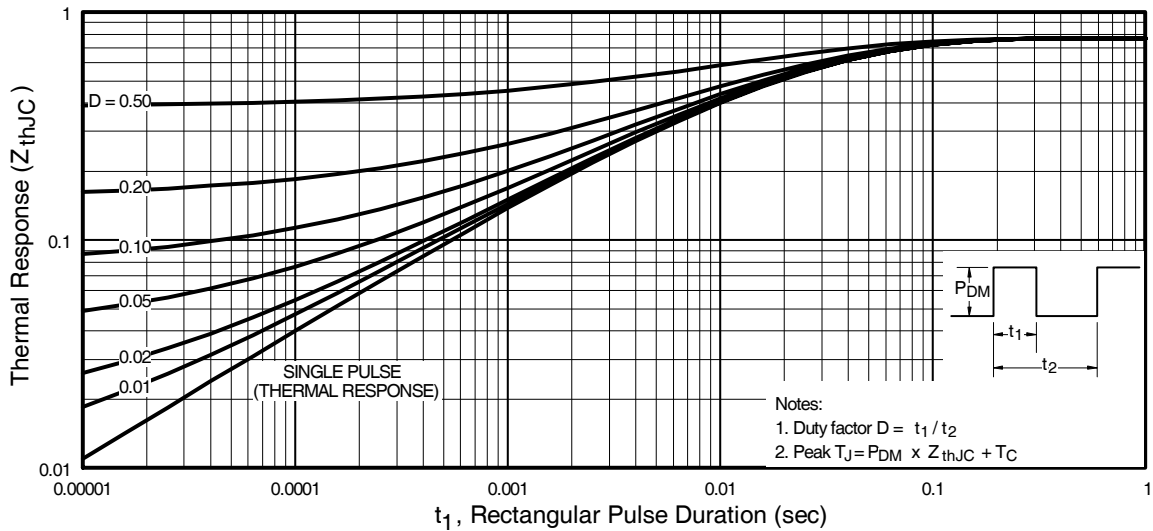
# IRG4PH40UD



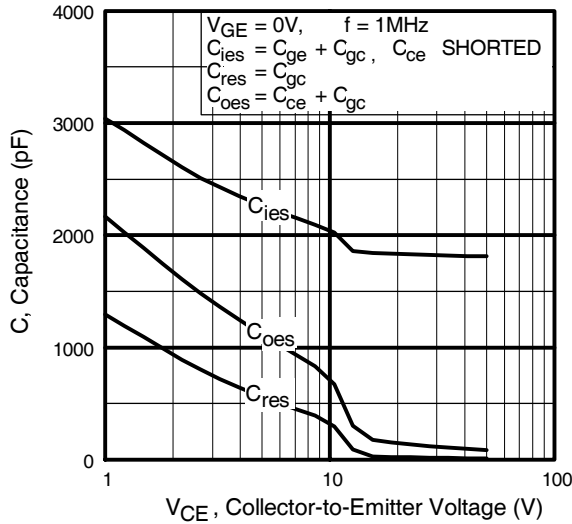
**Fig. 4 - Maximum Collector Current vs. Case Temperature**



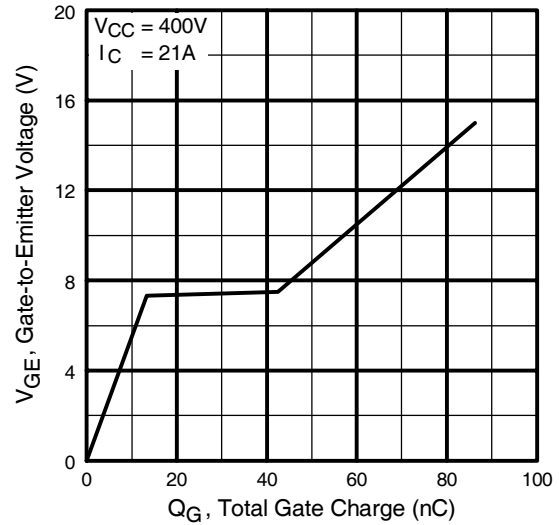
**Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature**



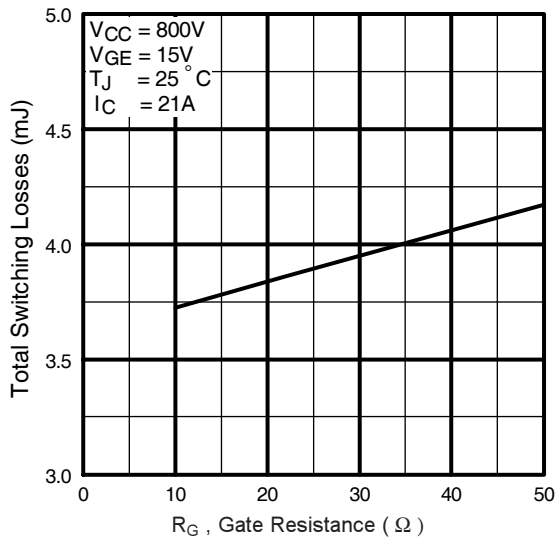
**Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**



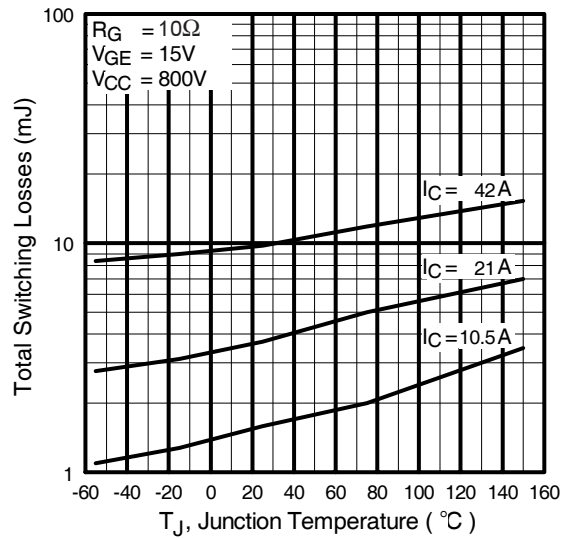
**Fig. 7** - Typical Capacitance vs. Collector-to-Emitter Voltage



**Fig. 8** - Typical Gate Charge vs. Gate-to-Emitter Voltage

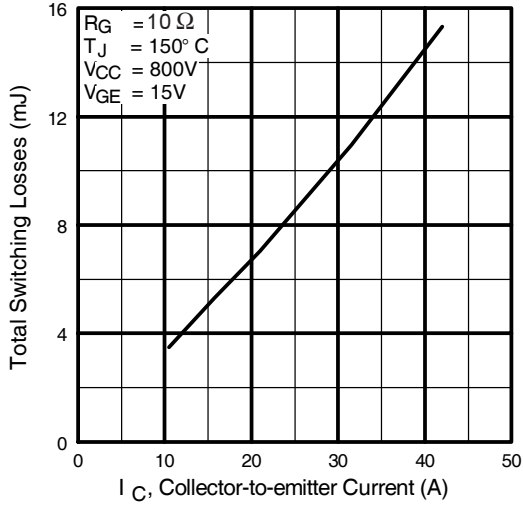


**Fig. 9** - Typical Switching Losses vs. Gate Resistance

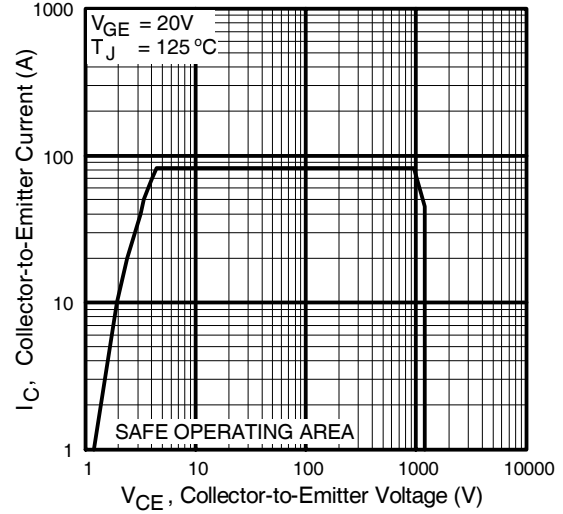


**Fig. 10** - Typical Switching Losses vs. Junction Temperature

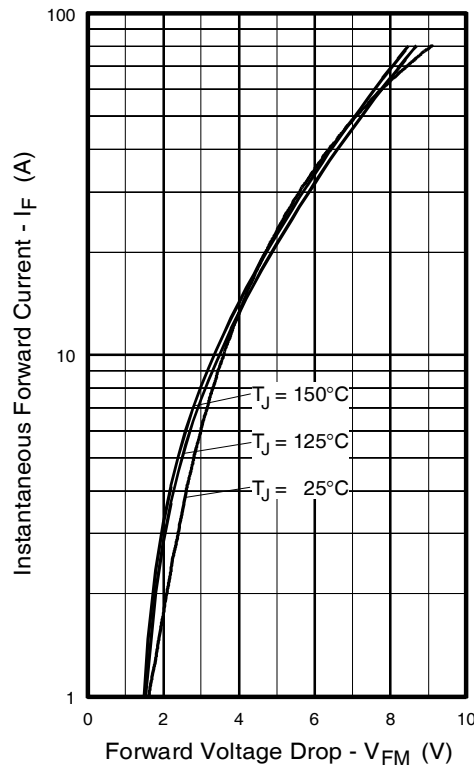
# IRG4PH40UD



**Fig. 11** - Typical Switching Losses vs. Collector-to-emitter Current



**Fig. 12** - Turn-Off SOA



**Fig. 13** - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

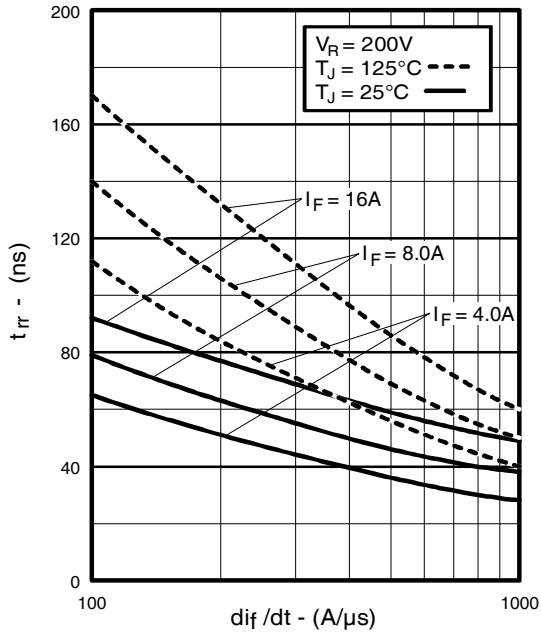


Fig. 14 - Typical Reverse Recovery vs.  $di_f/dt$

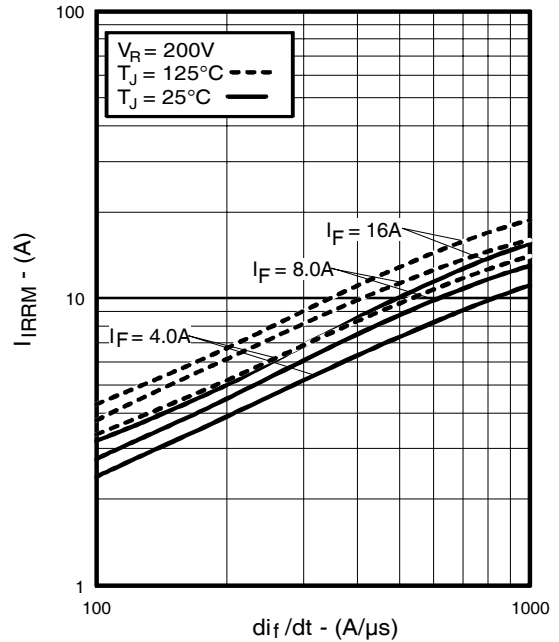


Fig. 15 - Typical Recovery Current vs.  $di_f/dt$

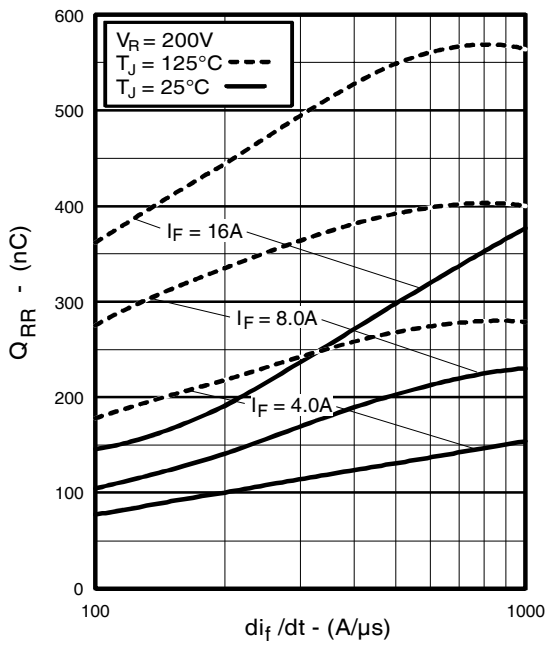


Fig. 16 - Typical Stored Charge vs.  $di_f/dt$

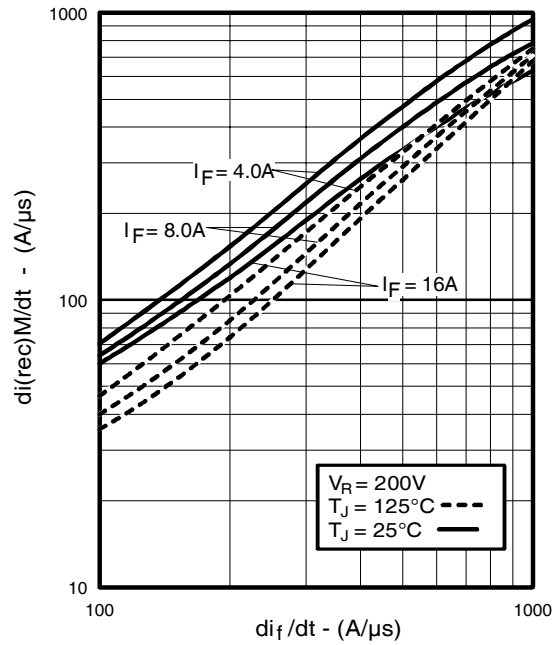
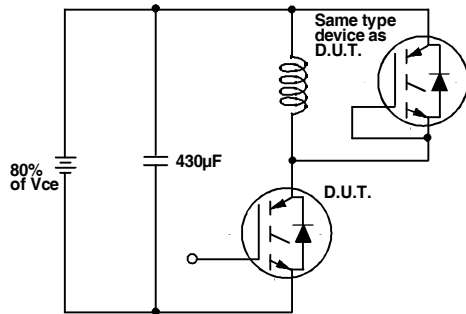
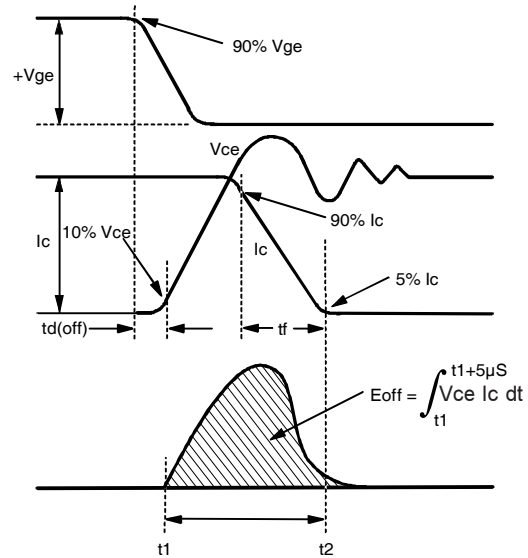


Fig. 17 - Typical  $di_{(rec)}M/dt$  vs.  $di_f/dt$

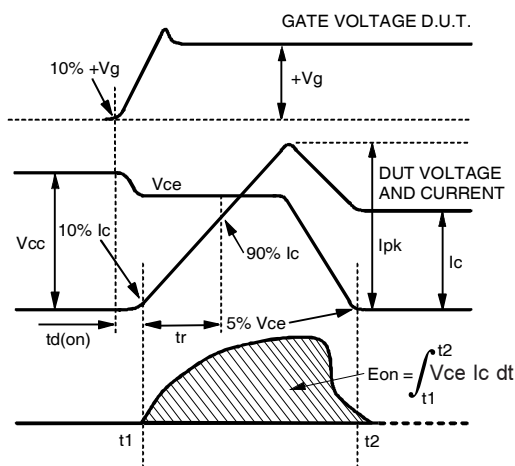
# IRG4PH40UD



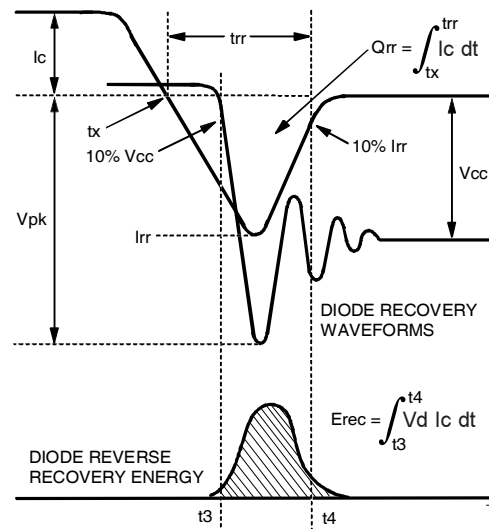
**Fig. 18a** - Test Circuit for Measurement of  $I_{LM}$ ,  $E_{on}$ ,  $E_{off}(\text{diode})$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$ ,  $t_{d(on)}$ ,  $t_r$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18b** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{off}$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18c** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{on}$ ,  $t_{d(on)}$ ,  $t_r$



**Fig. 18d** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{rec}$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$



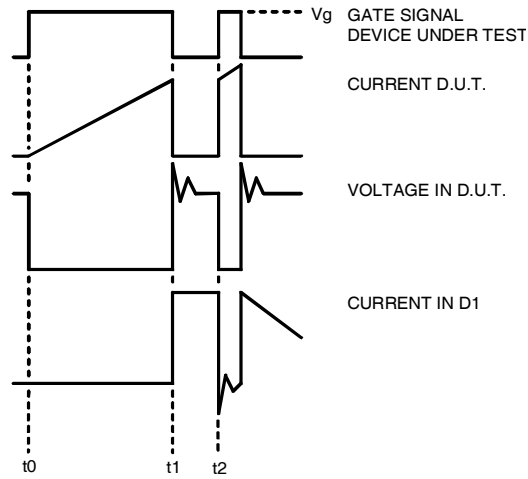


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

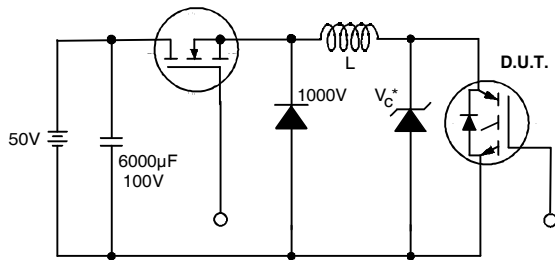


Figure 19. Clamped Inductive Load Test Circuit

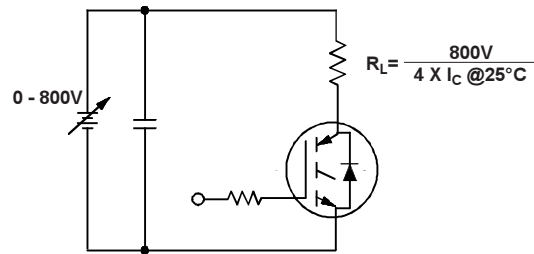


Figure 20. Pulsed Collector Current Test Circuit

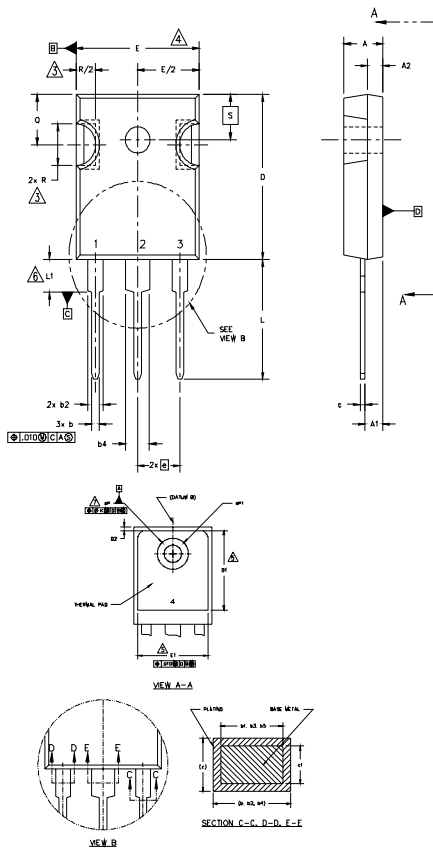
# IRG4PH40UD

## Notes:

- ① Repetitive rating:  $V_{GE}=20V$ ; pulse width limited by maximum junction temperature (figure 20)
- ②  $V_{CC}=80\%(V_{CES})$ ,  $V_{GE}=20V$ ,  $L=10\mu H$ ,  $R_G=10\Omega$  (figure 19)
- ③ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
- ④ Pulse width  $5.0\mu s$ , single shot.

## TO-247AC Package Outline

Dimensions are shown in millimeters (inches)



### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7.  $\phi P$  TO HAVE A MAXIMUM DRAFT ANGLE OF  $1.5^\circ$  TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154" [3.91].
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247 WITH THE EXCEPTION OF DIMENSION c.

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.37	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.034	0.38	0.86	
D	.776	.815	19.71	20.70	4
D1	.515	-	13.08	-	5
D2	.020	.030	0.51	0.76	4
E	.602	.625	15.29	15.87	
E1	.540	-	15.72	-	
e	.215 BSC		5.46 BSC		
$\phi k$	.010		2.54		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
N	3		7.62 BSC		
$\phi P$	.140	.144	3.56	3.66	
$\phi P1$	-	.275	-	6.98	
Q	.209	.224	5.31	5.69	
R	.178	.216	4.52	5.49	
S	.217 BSC		5.51 BSC		

### LEAD ASSIGNMENTS

#### HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

#### IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

#### DIODES

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

**TO-247AC package is not recommended for Surface Mount Application.**

Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>